REMARKS/ARGUMENTS

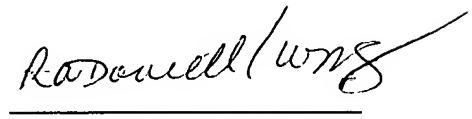
Claims 1 to 56 remain in this application.

Claims 1, 44 and 50, the Abstract and paragraphs from pages 5 and 7 of the description have been amended to clarify that the doped semiconductor nanocrystal layer comprises from 30 to 50 atomic percent of semiconductor elements, which semiconductor elements form both the oxide layer and the nanocrystals distributed in the oxide layer.

A person skilled in the art would readily appreciate that the concentration of from 30 to 50 atomic percent is related to the amount of semiconductor in the doped semiconductor nanocrystal layer, especially in light of the teachings of the reference by J. Sin, M. Kim, S. Seo, and C. Lee [Applied Physics Letters, (1998), Volume 72, 9, 1092-1094], which reference is incorporated by reference in the present application (see page 15, lines 21 to 25). The reference clearly states that the atomic ratio (1:2 to 2:1) is a ratio of silicon to oxygen. The fact that the concentrations expressed in the present application (e.g. 30 to 50 atomic percent) refer to a ratio of semiconductor (e.g. silicon) to other elements such as oxygen, as in the incorporated reference, is further supported by the observation that the "preferred", "more preferred" and "most preferred" percentages disclosed in the present application (e.g. on page 7 of the description) correlate directly with the ratios investigated in the incorporated reference.

Applicants respectfully submit that no new matter has been added.

Respectfully submitted,
DOWELL & DOWELL, P.C.



Ralph A. Dowell
Reg. No.: 26,868

DOWELL & DOWELL, P.C.
Suite 406, 2111 Eisenhower Avenue
Alexandria, Virginia 22314
Telephone: (703) 415-2555